

PSMN034-100PS

N-channel 100 V 34.5 m Ω standard level MOSFET in TO220.

Rev. 02 — 1 March 2010

Objective data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	100	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	32	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	86	W
Tj	junction temperature		-55	-	175	°C
Avalance	ne ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 32 A; $V_{sup} \le$ 100 V; unclamped; R_{GS} = 50 Ω	-	-	42	mJ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$	-	6.9	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 50 V; see <u>Figure 12</u> and <u>13</u>	-	23.8	-	nC
Static ch	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{\text{ constant}}$	-	-	62	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{16}{\text{Figure } 16}$	-	29.3	34.5	mΩ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		_G (EX)
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN034-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$	-	100	V
V_{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	22	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	-	32	Α
I_{DM}	peak drain current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	127	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	86	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
Source-dr	ain diode				
Is	source current	T _{mb} = 25 °C	-	32	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ} C$	-	127	Α
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 32 A; V_{sup} ≤ 100 V; unclamped; R_{GS} = 50 Ω	-	42	mJ

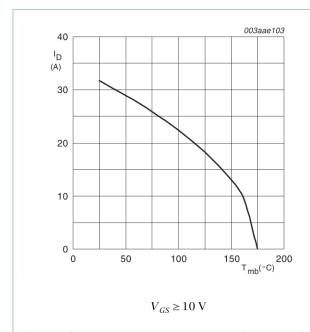


Fig 1. Continuous drain current as a function of mounting base temperature

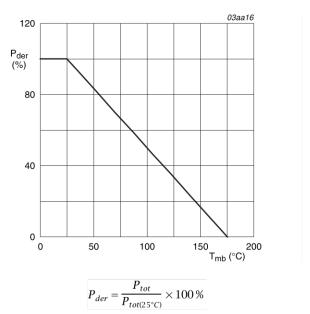


Fig 2. Normalized total power dissipation as a function of mounting base temperature

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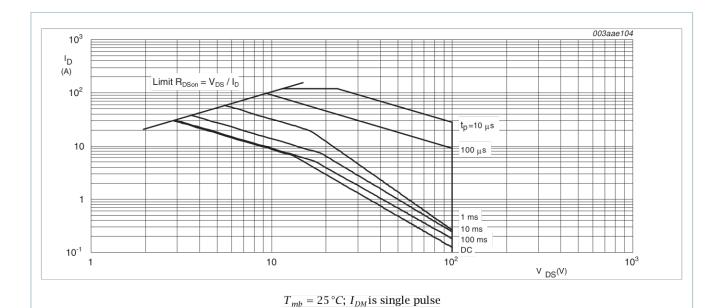


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.9	1.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	50	-	K/W

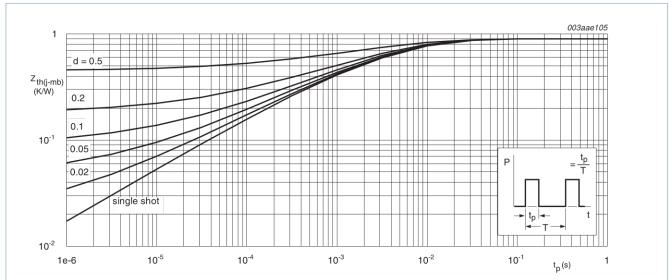


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6 Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _{(BR)DSS}	drain-source	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	90	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
V _{GS(th)}	gate-source threshold	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; see <u>Figure 9</u>	1	-	-	V
	voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 10</u> and <u>9</u>	2	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; see <u>Figure 9</u> and <u>10</u>	-	-	4.8	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	50	μΑ
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	10	100	nΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nΑ
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 ^{\circ}\text{C};$ see Figure 11	-	-	62	mΩ
		V_{GS} = 10 V; I_D = 15 A; T_j = 175 °C; see Figure 11	-	82.1	96	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 16</u>	-	29.3	34.5	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic cl	haracteristics					
Q _{G(tot)} total gate charge	total gate charge	I_D = 15 A; V_{DS} = 50 V; V_{GS} = 10 V; see <u>Figure 12</u> and <u>13</u>	-	23.8	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	19	-	nC
Q_{GS}	gate-source charge	I _D = 15 A; V _{DS} = 50 V; V _{GS} = 10 V; see <u>Figure 12</u> and <u>13</u>	-	5.5	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	I_D = 15 A; V_{DS} = 50 V; V_{GS} = 10 V; see <u>Figure 12</u>	-	3.6	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	1.9	-	nC
Q_{GD}	gate-drain charge	I_D = 15 A; V_{DS} = 50 V; V_{GS} = 10 V; see <u>Figure 12</u> and <u>13</u>	-	6.9	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V_{DS} = 50 V; see <u>Figure 12</u> and <u>13</u>	-	4.4	-	V
C _{iss}	input capacitance	V_{DS} = 50 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C;	-	1201	-	рF
C _{oss}	output capacitance	see <u>Figure 14</u>	-	94	-	рF
C _{rss}	reverse transfer capacitance		-	61	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 50 V; R_{L} = 3.3 Ω ; V_{GS} = 10 V;	-	12	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 °C$	-	10	-	ns
$t_{d(off)}$	turn-off delay time		-	28	-	ns
t _f	fall time	_	_	9	_	ns

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dr	ain diode					
V_{SD}	source-drain voltage	I_S = 15 A; V_{GS} = 0 V; T_j = 25 °C; see <u>Figure 17</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	38	-	ns
Q_r	recovered charge	$V_{DS} = 50 \text{ V}$	-	59	-	nC

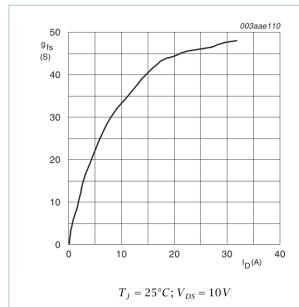


Fig 5. Forward transconductance as a function of drain current; typical values

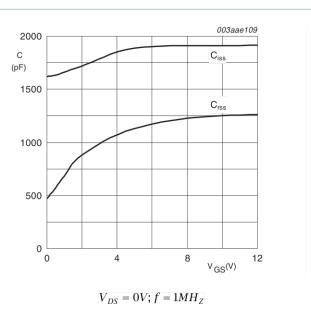


Fig 6. Input and reverse capacitances as a function of gate-source voltage; typical values

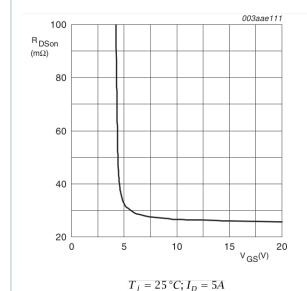


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

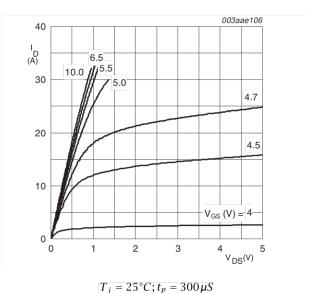


Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values

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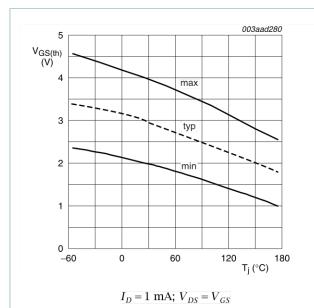
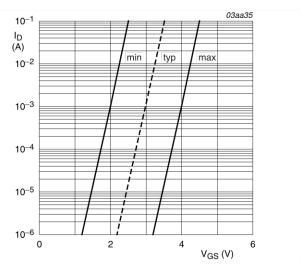


Fig 9. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

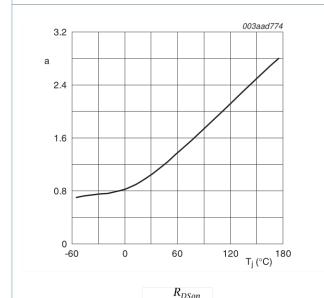


Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature

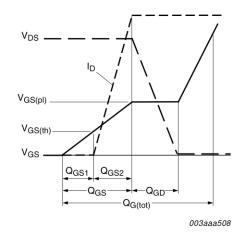


Fig 12. Gate charge waveform definitions

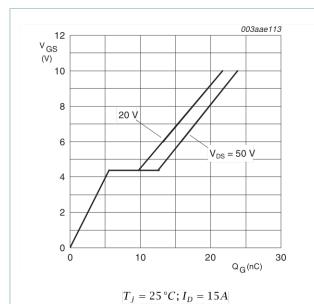
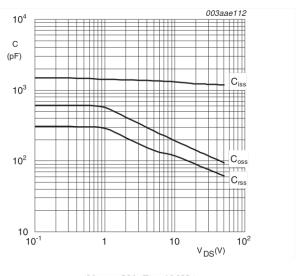


Fig 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V$; $F = 1MH_Z$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

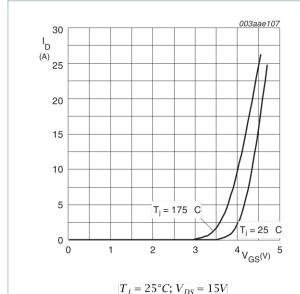
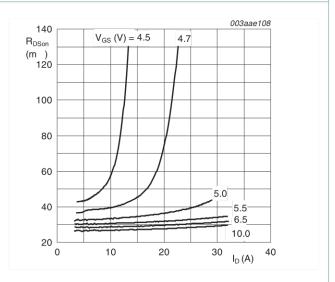
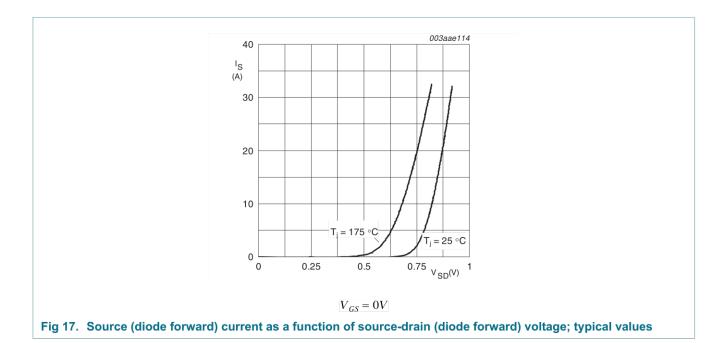


Fig 15. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25^{\circ}C$; $t_p = 300\mu S$

Fig 16. Drain-source on-state resistance as a function of drain current; typical values



Package outline

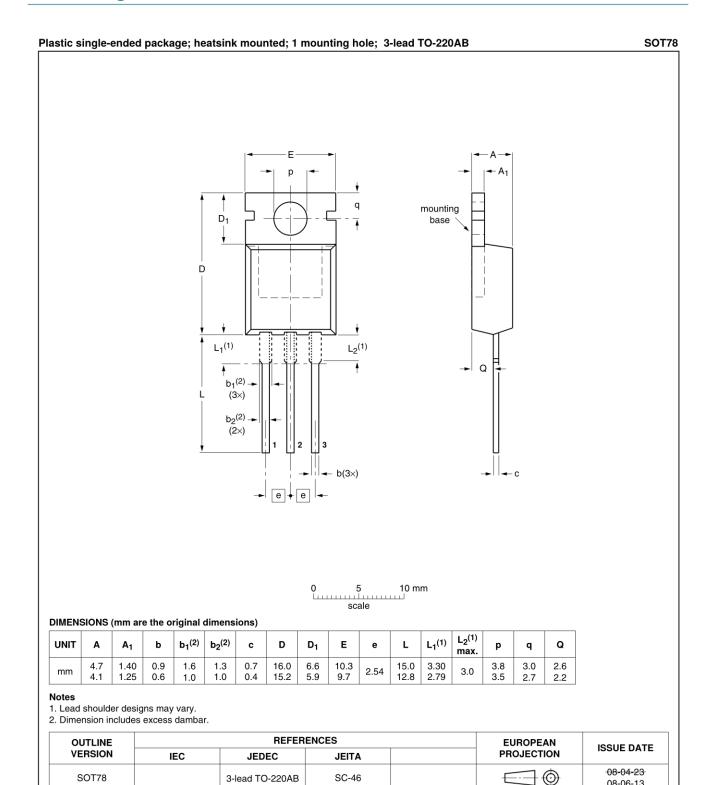


Fig 18. Package outline SOT78 (TO-220AB)

08-06-13

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN034-100PS_2	20100301	Objective data sheet	-	PSMN034-100PS_1
Modifications:	 Various ch 	anges to content.		
PSMN034-100PS_1	20100218	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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